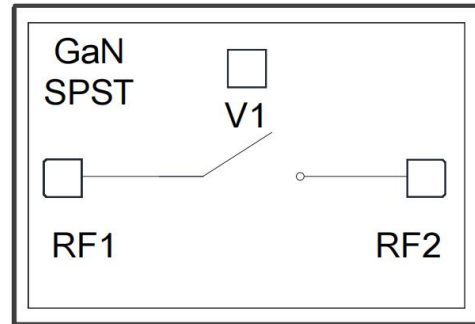


Performance

- Frequency: 0.1~20GHz
- Insertion loss: 0.8dB
- Isolation: 40dB
- Input P-0.3: 47dBm
- Input/Output VSWR: 1.3:1
- Switching Time: 20ns
- Control Mode: 0/-40V
- Voltage control reflective switch
- Chip size: 1.8*0.9*0.08mm

Function Diagram



Electrical Specifications (Ta=+25°C, V1~V2=0V/-40V, F=0.1~20GHz)

Symbol	Parameter	Min.	Typ.	Max.	Unit
Li	Insertion Loss	-	0.8	-	dB
ISO	Isolation	-	40	-	dB
VSWR	Input / Output VSWR	-	1.3	-	-

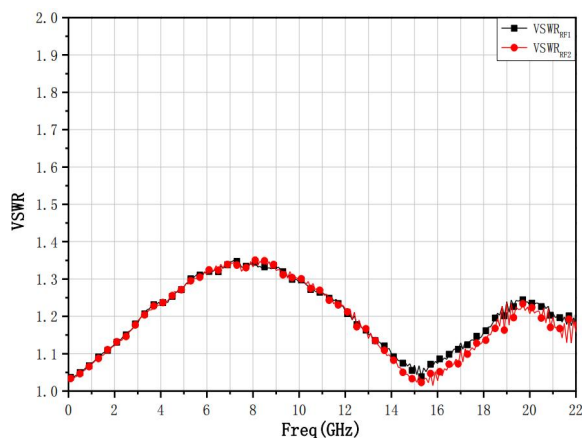
Absolute Maximum Ratings (Ta=+25°C)

Symbol	Parameter	Value	Notes
V1,2	Control Voltage	-60V	
Pcw	Input Continuous Wave Power	47.5dBm	
Tch	Channel Temperature	225°C	
T	Sintering Temperature	310°C	30s, N2 protection
Tstg	Storage Temperature	-65~150°C	

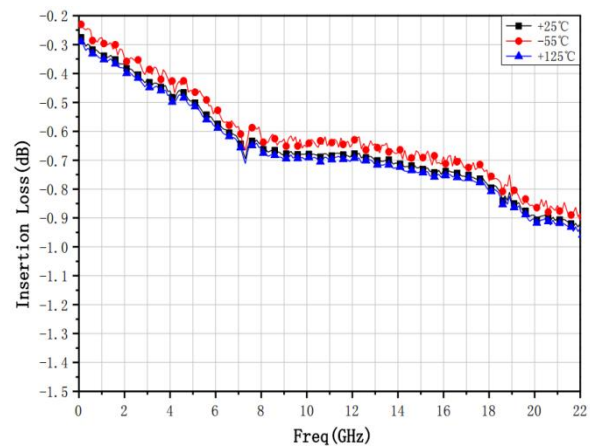
Exceed any of above listed ratings may cause permanent damage.

Test Curves (Ta=+25°C, (V1=-40V))

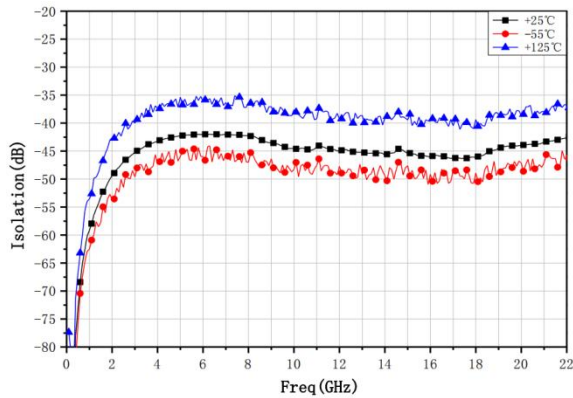
VSWR



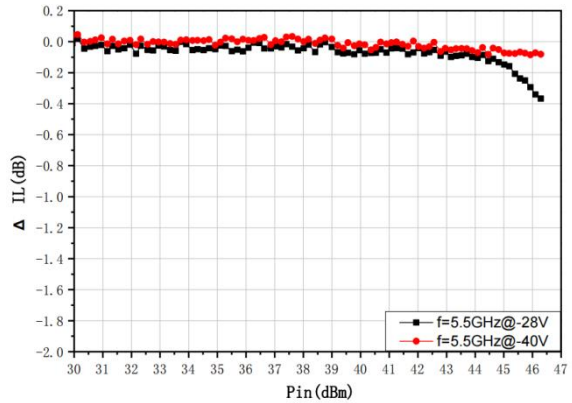
Insertion Loss @ Different temperature



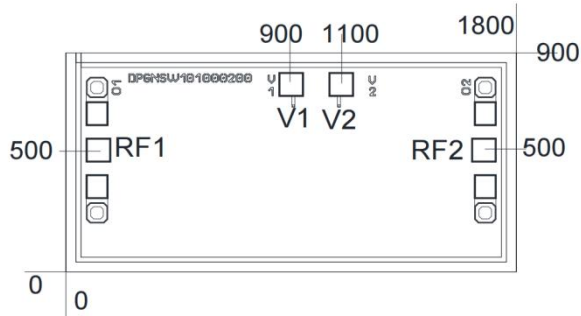
Isolation @ Different Temperature



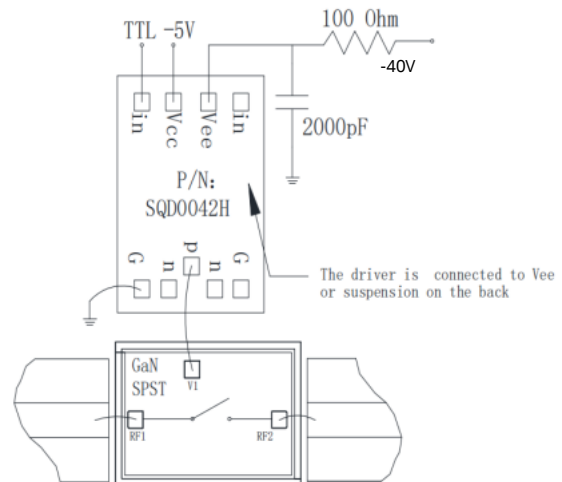
Input Power (Y axis is normalized value of I.L)



Outline Size (μm)



Assembly Diagram



PIN Definition

PIN	Description
RF1、RF2	RF ports, 50Ω, no block capacitor
V1、V2	Control Ports
GND	Bottom must be grounded

Truth Table

V1	V2	RF1→RF2
1	0	ON
0	1	OFF

Note: 1. Low level "0" is -28V~-40V, High level "1" is 0V~0.5V

2. Performance is same under condition of -28V ~ -40V

Note

- a) Sinter with 80/20 gold tin, with a sintering temperature not exceeding 300 °C and a sintering time as short as possible, not exceeding 30 seconds;
- b) Chips are electrostatic sensitive devices, and attention should be paid to anti-static measures during use, transportation, and operation;
- c) 2 bonding wires (diameter 25) for input and output μ M gold wire, bonding wire length 350 μ Around m is optimal;
- d) This product is a hydrogen sensitive device with a hydrogen resistance of 20000ppm. It is recommended to pay attention to controlling the hydrogen concentration in the sealed chamber during use.